Taiwan Semiconductor

## **N-Channel Power MOSFET**

30V, 62A, 6mΩ

#### **FEATURES**

- Low R<sub>DS(ON)</sub> to minimize conductive Loss
- Low gate charge for fast power switching
- 100% UIS and R<sub>g</sub> tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

PRODUCT SUMMARY				
PARAMETER		VALUE	UNIT	
$V_{ t DS}$		30	٧	
R <sub>DS(on)</sub> (max)	$V_{GS} = 10V$	6	•	
	$V_{GS} = 4.5V$	9	mΩ	
$Q_g$		12.9	nC	





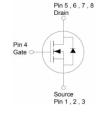


#### **APPLICATIONS**

- DC-DC Converters
- Battery Power Management
- Oring FET/Load Switch

PDFN33





Notes: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	30	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	ļ	62	Α	
Continuous Drain Current	$T_A = 25^{\circ}C$	l <sub>D</sub>	15		
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	248	Α	
Single Pulse Avalanche Current (Note 2)		I <sub>AS</sub>	29	Α	
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	42	mJ	
Total Power Discinstion	$T_C = 25^{\circ}C$	D	40	W	
Total Power Dissipation	T <sub>C</sub> = 125°C	$P_{D}$	8	VV	
Total Power Dissipation	$T_A = 25$ °C	В	2.3	W	
Total Power Dissipation	T <sub>A</sub> = 125°C	$P_{D}$	0.5	VV	
Operating Junction and Storage Temperature Range		$T_J, T_STG$	- 55 to +150	°C	

THERMAL RESISTANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Thermal Resistance – Junction to Case	R <sub>eJC</sub>	3.1	°C/W	
Thermal Resistance – Junction to Ambient	R <sub>eJA</sub>	53	°C/W	

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.

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ELECTRICAL CHARACTERISTICS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	$V_{GS(TH)}$	1.2	1.6	2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	I <sub>GSS</sub>			±100	nA
Drain-Source Leakage Current	$V_{GS}=0V,\ V_{DS}=30V$	I <sub>DSS</sub>			1	μΑ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 15A$	_		4.8	6	mΩ
(Note 3)	$V_{GS} = 4.5V, I_D = 15A$	$R_{DS(on)}$		6.7	9	
Forward Transconductance (Note 3)	$V_{DS} = 5V, I_{D} = 15A$	g <sub>fs</sub>		38		S
Dynamic (Note 4)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 15V,$ $I_{D} = 15A$	$Q_g$		25.4		
Total Gate Charge	$V_{GS} = 4.5V, V_{DS} = 15V,$	$Q_{g}$		12.9		nC
Gate-Source Charge		$Q_gs$		3.8		
Gate-Drain Charge	I <sub>D</sub> = 15A	$Q_{gd}$		5.7		
Input Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$	C <sub>iss</sub>		1342		
Output Capacitance		C <sub>oss</sub>		227		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		169		
Gate Resistance	f = 1.0MHz, open drain	$R_g$	0.8	2.7	5.4	Ω
Switching (Note 4)						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 15V,$ $I_{D} = 15A, R_{G} = 3.3\Omega,$	t <sub>d(on)</sub>		7.5		
Rise Time		t <sub>r</sub>		14.5		
Turn-Off Delay Time		t <sub>d(off)</sub>		35.2		ns
Fall Time		t <sub>f</sub>		9.6		
Source-Drain Diode						
Diode Forward Voltage (Note 3)	$V_{GS} = 0V, I_{S} = 15A$	V <sub>SD</sub>			1	V
Reverse Recovery Time	I <sub>S</sub> = 15A,	t <sub>rr</sub>		8.8		ns
Reverse Recovery Charge	di/dt = 100A/μs	Q <sub>rr</sub>		26		nC

#### Notes:

- 1. Current limited by package.
- 2.  $L=0.1mH,~V_{GS}=10V,~V_{DS}=25V,~R_{G}$  = 25 $\Omega,~I_{AS}=29A,~Starting~T_{J}=25^{\circ}C$
- 3. Pulse test: Pulse Width  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%.
- 4. Switching time is essentially independent of operating temperature.

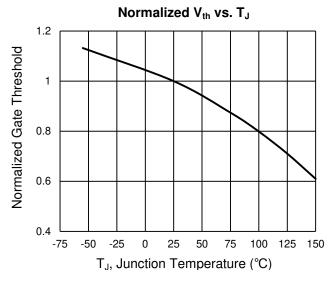
#### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM060N03PQ33 RGG	PDFN33	5,000pcs / 13" Reel

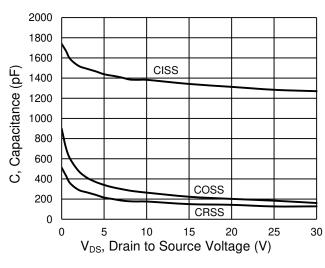


#### **CHARACTERISTICS CURVES**

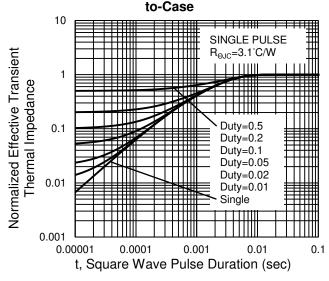
(T<sub>A</sub> = 25°C unless otherwise noted)



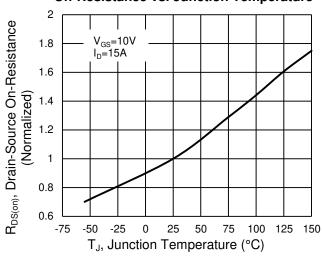
#### Capacitance vs. Drain-Source Voltage



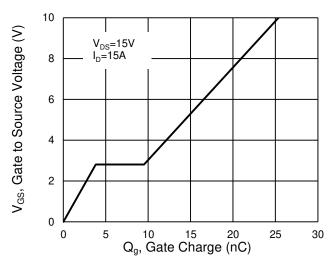
# Normalized Thermal Transient Impedance, Junction-



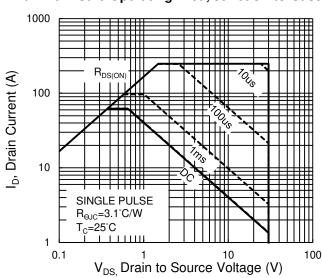
#### **On-Resistance vs. Junction Temperature**



#### Gate-Source Voltage vs. Gate Charge



#### Maximum Safe Operating Area, Junction-to-Case



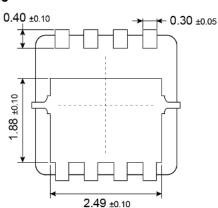
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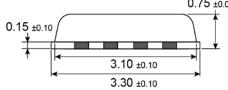
3



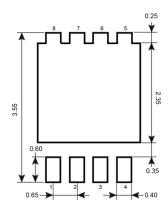
#### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

# 0.40 0.40 0.05 (REF) 0.75 ±0.05





## SUGGESTED PAD LAYOUT (Unit: Millimeters)



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#### **MARKING DIAGRAM**



Y = Year Code

**M** = Month Code for Halogen Free Product

 $\mathbf{O}$  =Jan  $\mathbf{P}$  =Feb  $\mathbf{Q}$  =Mar  $\mathbf{R}$  =Apr

S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code (1~9, A~Z)



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